

WHAT IS CLAIMED IS:

1. A method of manufacturing a semiconductor device,
comprising the steps of:
 forming an island shape semiconductor film over a substrate; forming a first insulating film on the island shape semiconductor film;
 forming an island shape gate electrode and a capacitor wiring;
 forming a second insulating film covering the gate electrode and the capacitor wiring;
 forming a first contact hole to reach the gate electrode by selectively etching the second insulating film;
 forming a scanning line to be connected to the gate electrode on the second insulating film;
 forming a third insulating film on the scanning line;
 forming a second contact hole to reach the semiconductor film by selectively etching the third insulating film; and
 forming a signal line to be electrically connected to the semiconductor film.